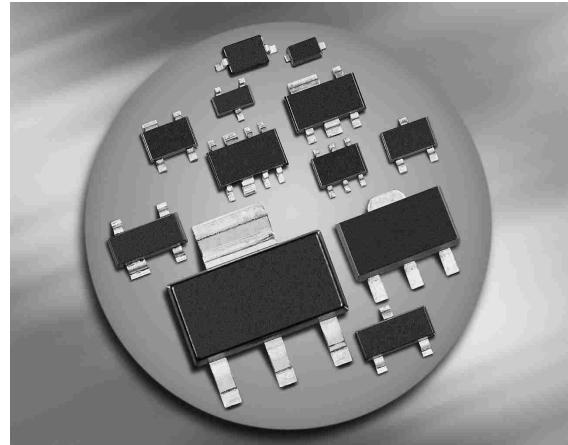


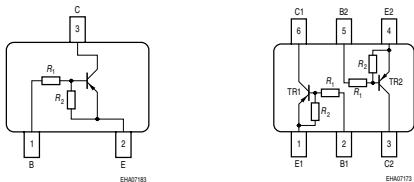
### PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ( $R_1 = 22\text{k}\Omega$ ,  $R_2 = 22\text{k}\Omega$ )
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



**BCR191/F/L3**  
**BCR191T/W**

**BCR191S**  
**SEMB1**



Type	Marking	Pin Configuration							Package
BCR191	WOs	1=B	2=E	3=C	-	-	-	-	SOT23
BCR191F	WOs	1=B	2=E	3=C	-	-	-	-	TSFP-3
BCR191L3	WO	1=B	2=E	3=C	-	-	-	-	TSLP-3-4
BCR191S	WOs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	-	SOT363
BCR191T	WOs	1=B	2=E	3=C	-	-	-	-	SC75
BCR191W	WOs	1=B	2=E	3=C	-	-	-	-	SOT323
SEMB1	WO	1=E1	2=B2	3=C2	4=E2	5=B2	6=C1	-	SOT666

**Maximum Ratings**

<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Emitter-base voltage	$V_{EBO}$	10	
Input on voltage	$V_{i(on)}$	30	
Collector current	$I_C$	100	mA
Total power dissipation- BCR191, $T_S \leq 102^\circ\text{C}$ BCR191F, $T_S \leq 128^\circ\text{C}$ BCR191L3, $T_S \leq 135^\circ\text{C}$ BCR191S, $T_S \leq 115^\circ\text{C}$ BCR191T, $T_S \leq 109^\circ\text{C}$ BCR191W, $T_S \leq 124^\circ\text{C}$ SEMB1, $T_S \leq 75^\circ\text{C}$	$P_{tot}$	200 250 250 250 250 250 250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	150 ... -65	

**Thermal Resistance**

<b>Parameter</b>	<b>Symbol</b>	<b>Value</b>	<b>Unit</b>
Junction - soldering point <sup>1)</sup> BCR191 BCR191F BCR191L3 BCR191S BCR191T BCR191W SEMB1	$R_{thJS}$	$\leq 240$ $\leq 90$ $\leq 60$ $\leq 140$ $\leq 165$ $\leq 105$ $\leq 300$	K/W

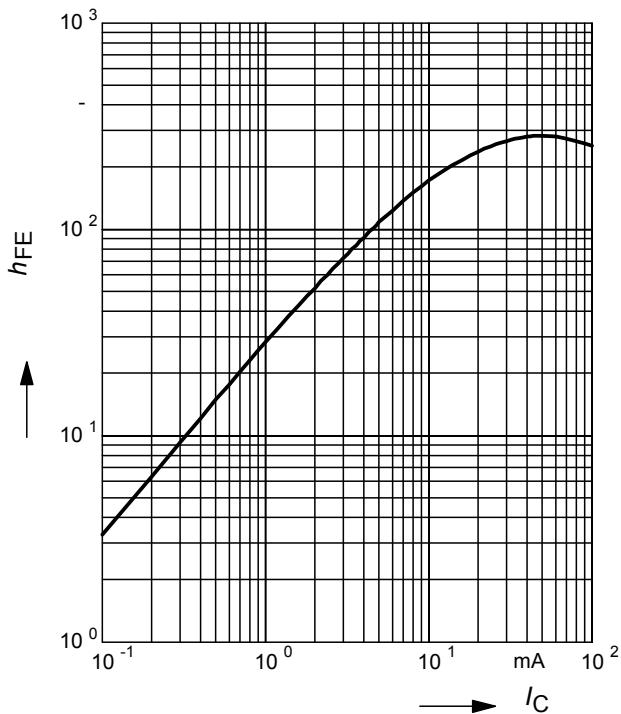
<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

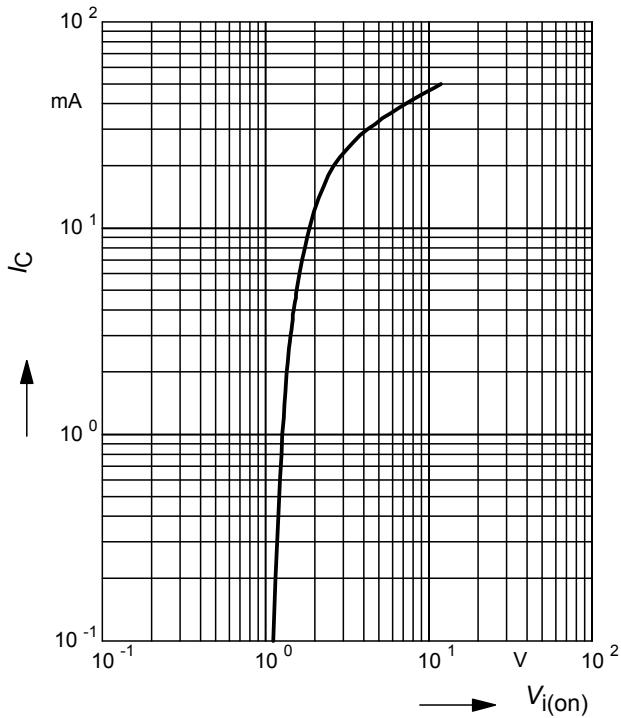
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{\text{CBO}}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	350	$\mu\text{A}$
DC current gain <sup>1)</sup> $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{\text{FE}}$	50	-	-	-
Collector-emitter saturation voltage <sup>1)</sup> $I_C = 10 \text{ mA}, I_B = 0,5 \text{ mA}$	$V_{\text{CEsat}}$	-	-	0,3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(\text{off})}$	0,8	-	1,5	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0,3 \text{ V}$	$V_{i(\text{on})}$	1	-	2,5	
Input resistor	$R_1$	15	22	29	k $\Omega$
Resistor ratio	$R_1/R_2$	0,9	1	1,1	-
<b>AC Characteristics</b>					
Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

<sup>1</sup>Pulse test:  $t < 300\mu\text{s}$ ;  $D < 2\%$

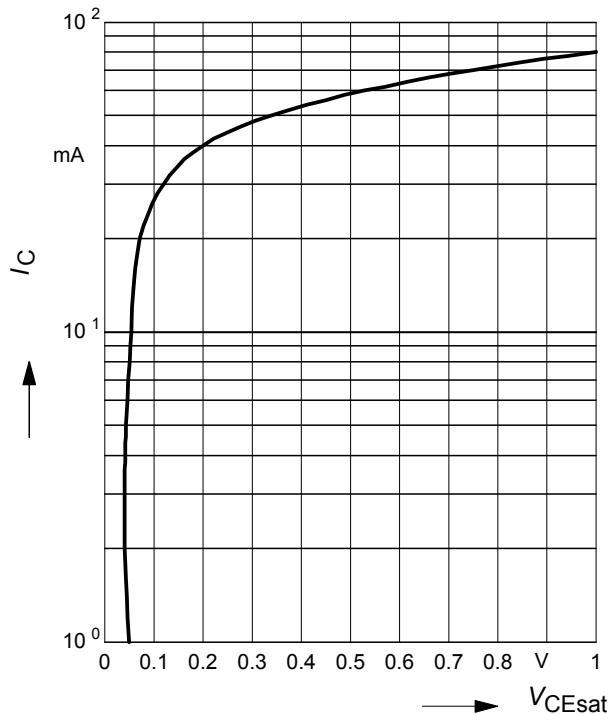
**DC current gain  $h_{FE} = f(I_C)$**   
 $V_{CE} = 5 \text{ V}$  (common emitter configuration)



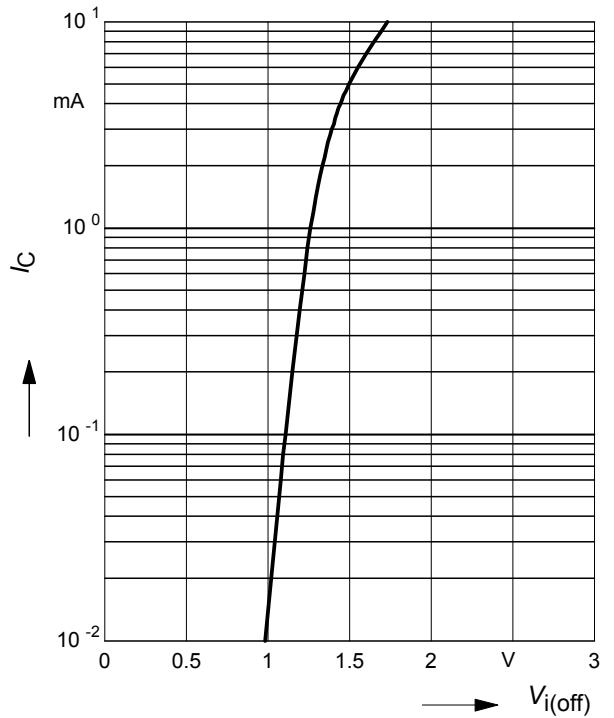
**Input on Voltage  $V_{i(on)} = f(I_C)$**   
 $V_{CE} = 0.3 \text{ V}$  (common emitter configuration)



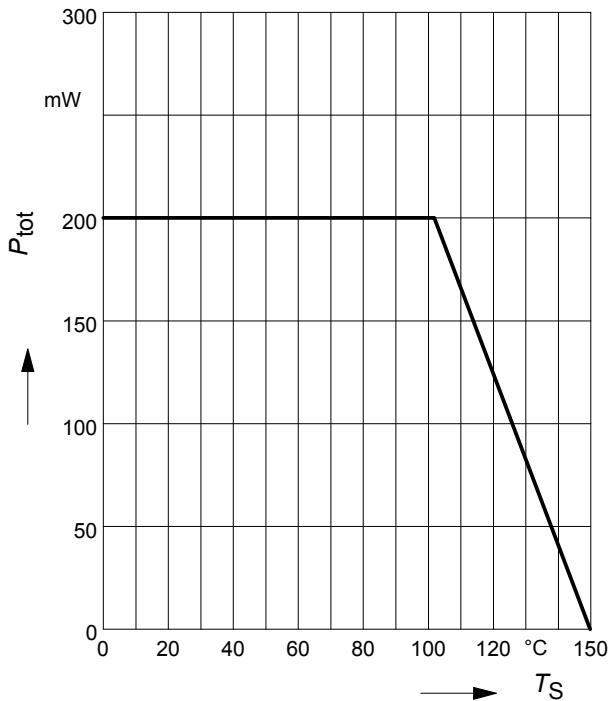
**Collector-emitter saturation voltage**  
 $V_{CEsat} = f(I_C)$ ,  $h_{FE} = 20$



**Input off voltage  $V_{i(off)} = f(I_C)$**   
 $V_{CE} = 5 \text{ V}$  (common emitter configuration)

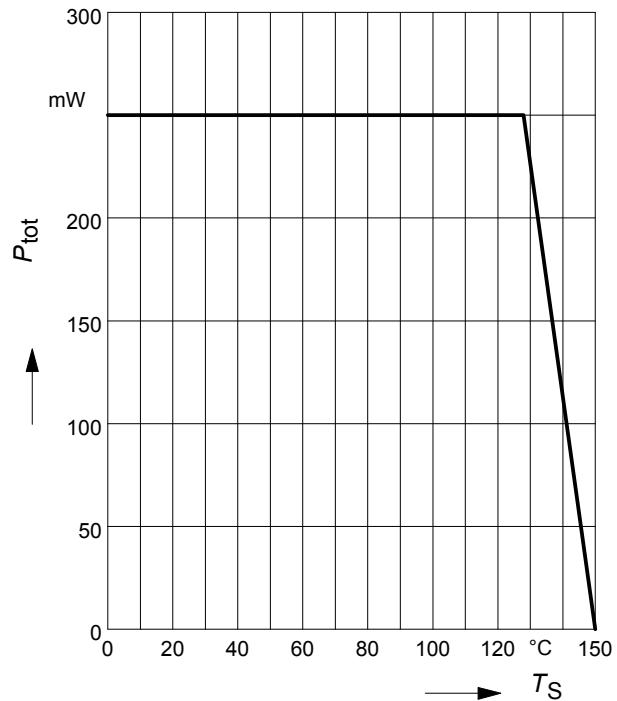


**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR191



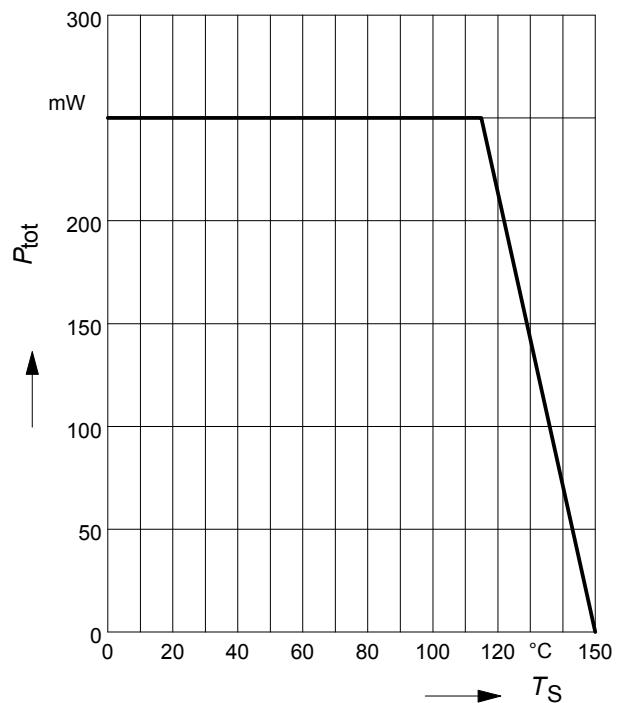
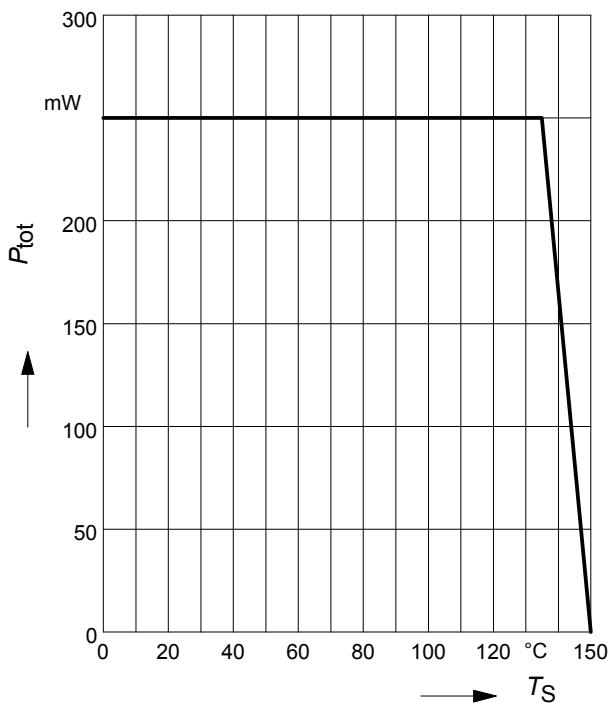
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR191F

**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR191F



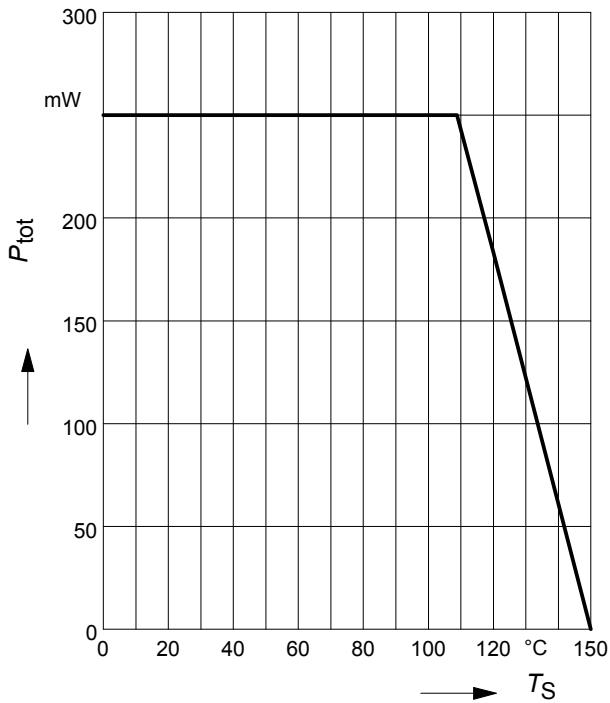
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR191L3

**Total power dissipation  $P_{\text{tot}} = f(T_S)$**   
BCR191S



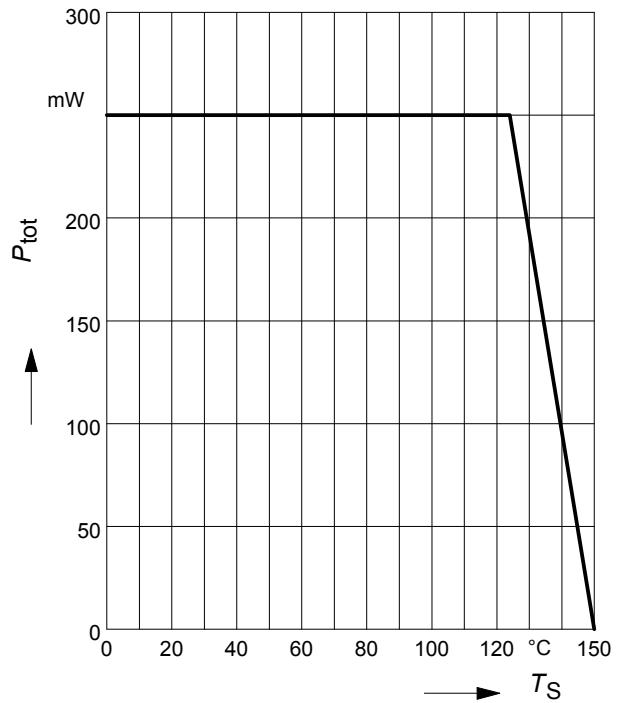
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

BCR191T



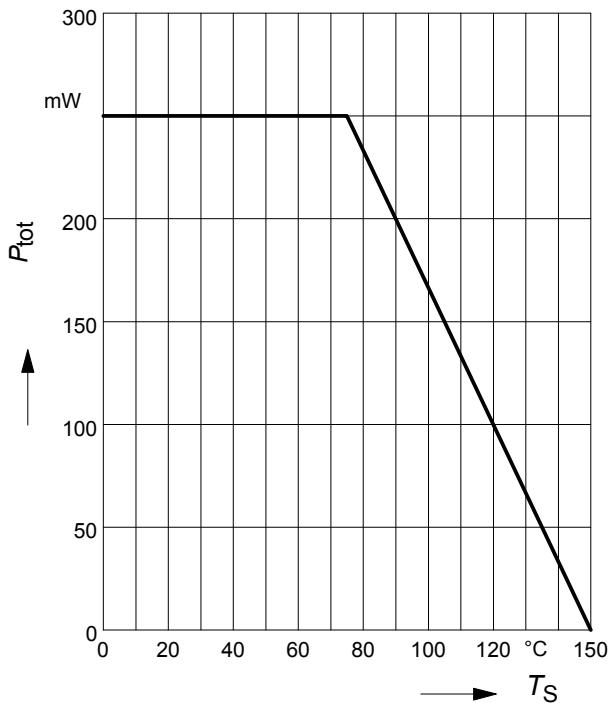
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

BCR191W



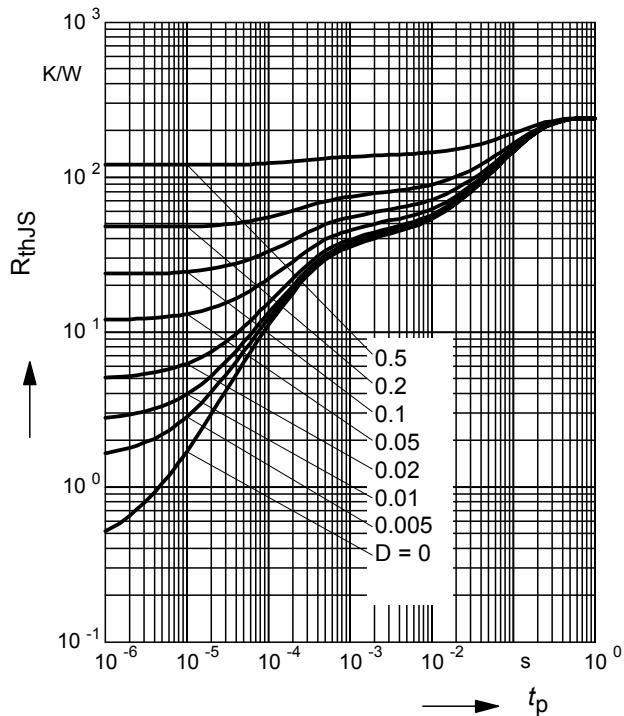
**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

SEMB1



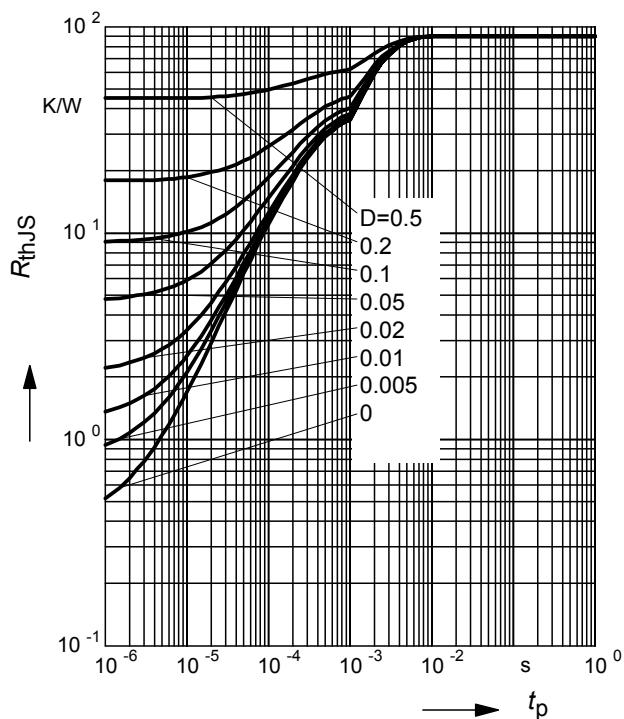
**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$

BCR191



**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$

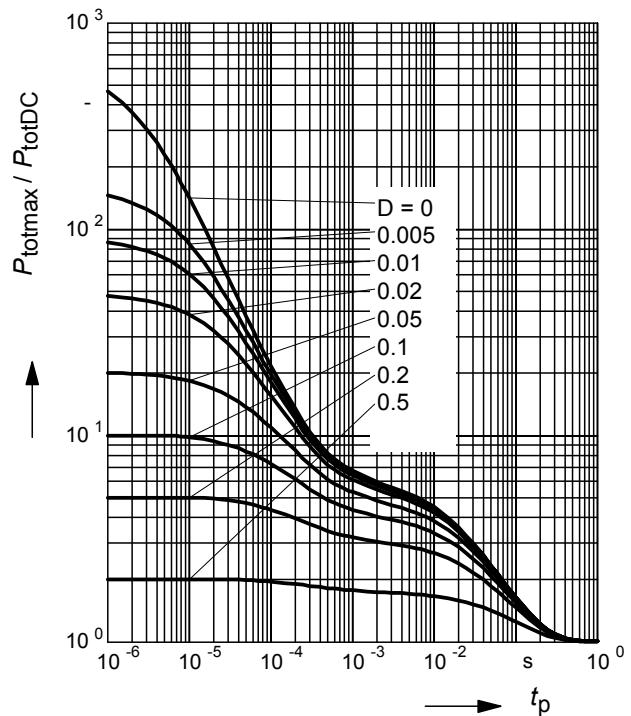
BCR191F



**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

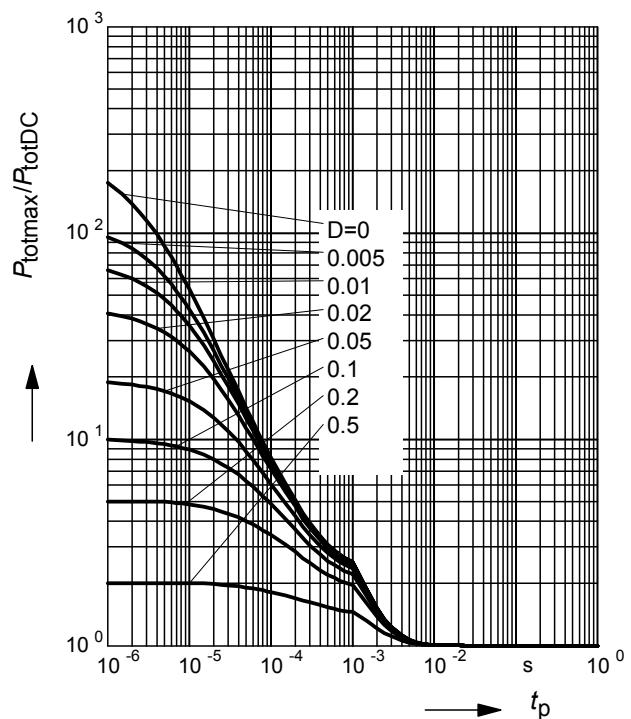
BCR191



**Permissible Pulse Load**

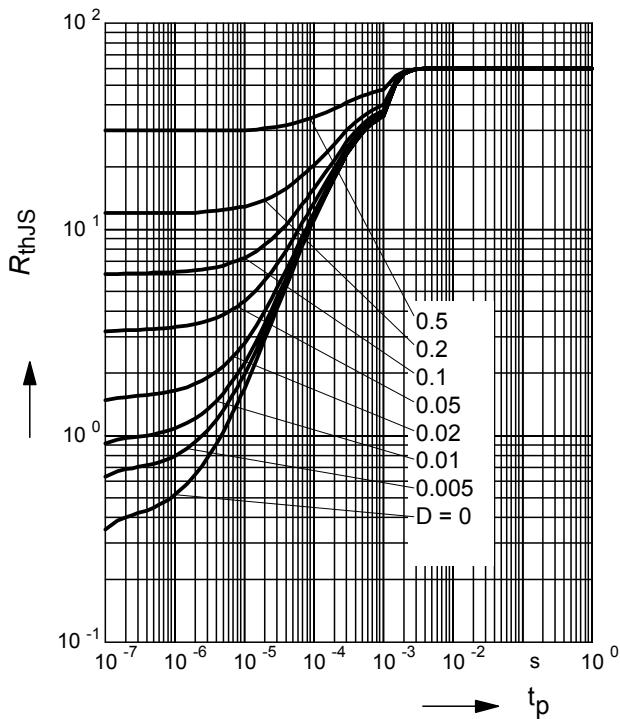
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BCR191F



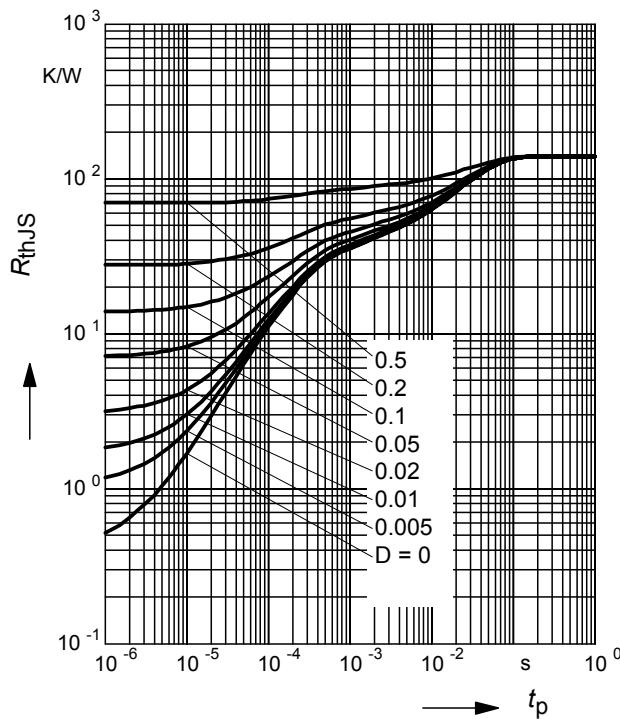
**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$

BCR191L3



**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$

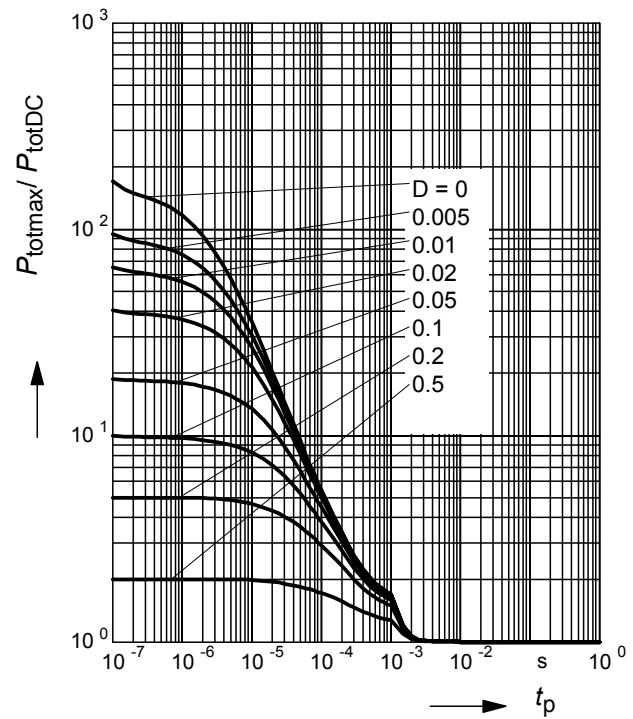
BCR191S



**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

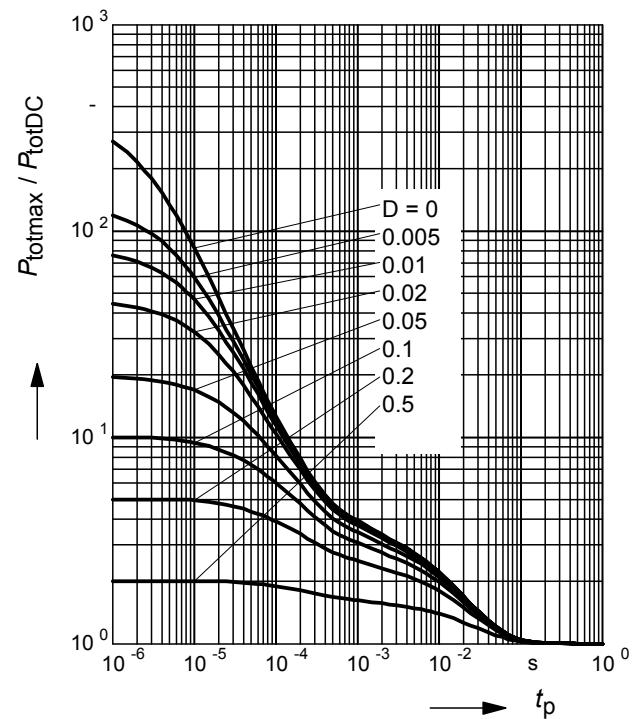
BCR191L3



**Permissible Pulse Load**

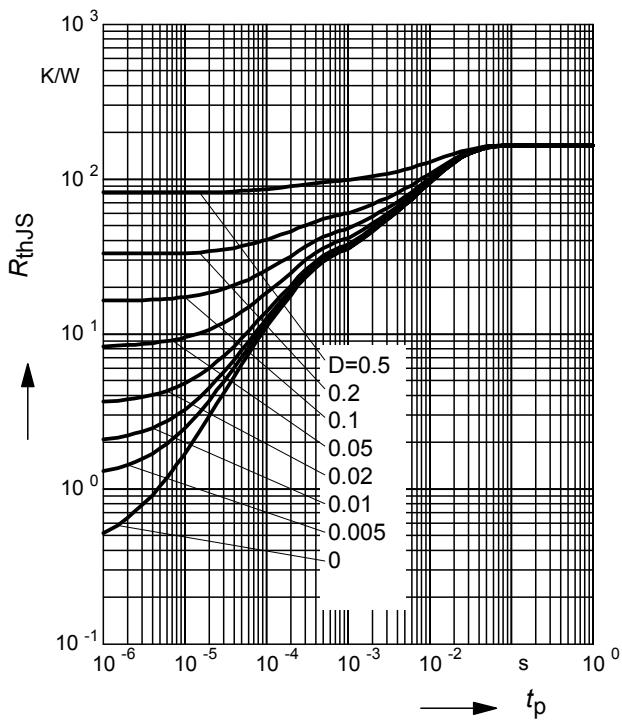
$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

BCR191S

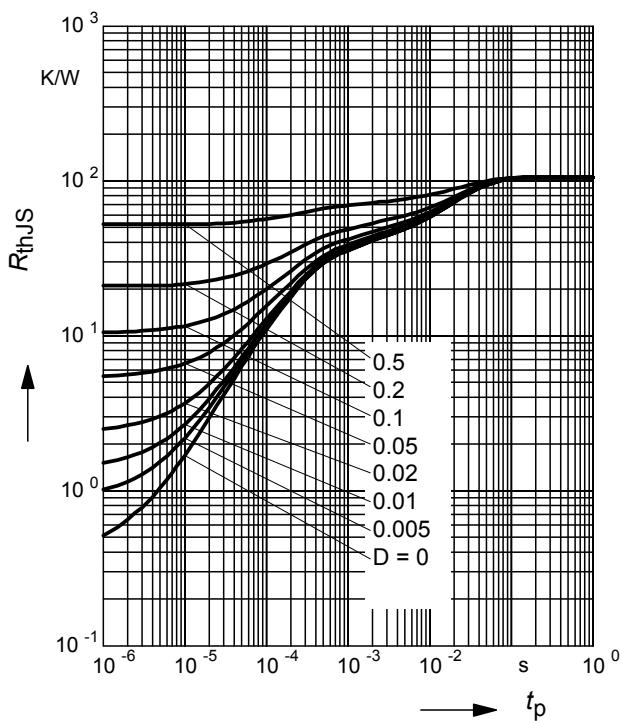


**Permissible Puls Load  $R_{thJS} = f(t_p)$** 

BCR191T

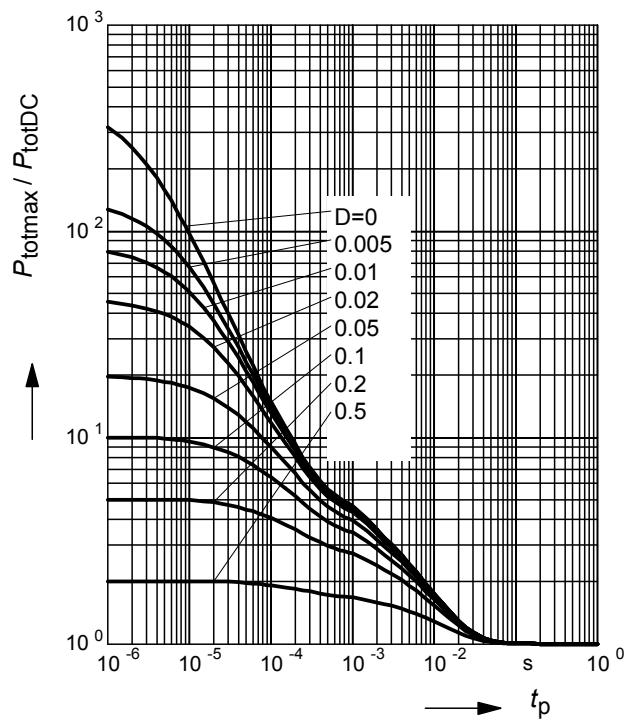

**Permissible Puls Load  $R_{thJS} = f(t_p)$** 

BCR191W


**Permissible Pulse Load**

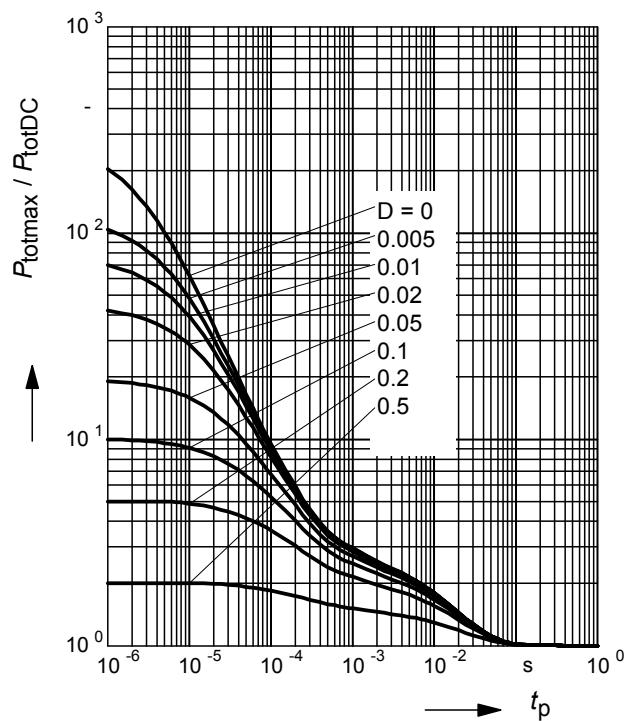
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR191T


**Permissible Pulse Load**

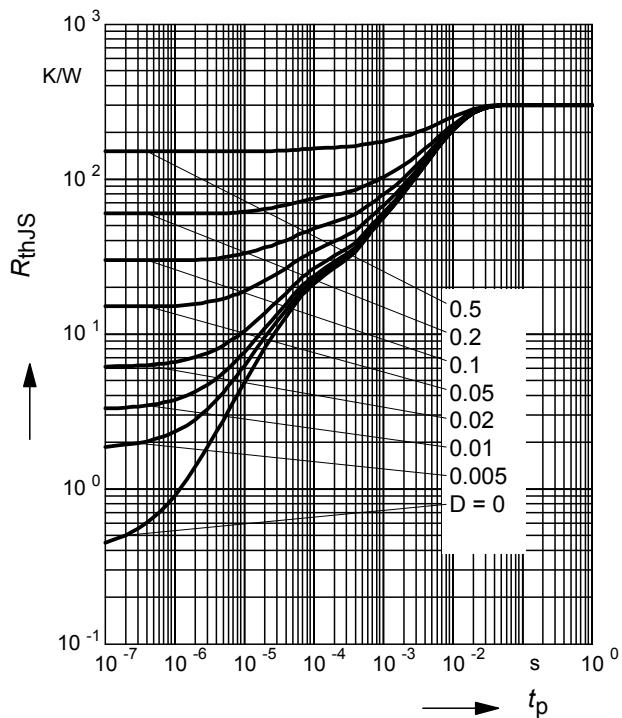
$$P_{totmax}/P_{totDC} = f(t_p)$$

BCR191W



**Permissible Puls Load**  $R_{\text{thJS}} = f(t_p)$

SEMB1



**Permissible Pulse Load**

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$

SEMB1

